

### BD034 TRANSISTOR (PNP)

#### FEATURES

Power dissipation

$P_{CM}$ : 1.25 W ( $T_{amb}=25^{\circ}C$ )

Collector current

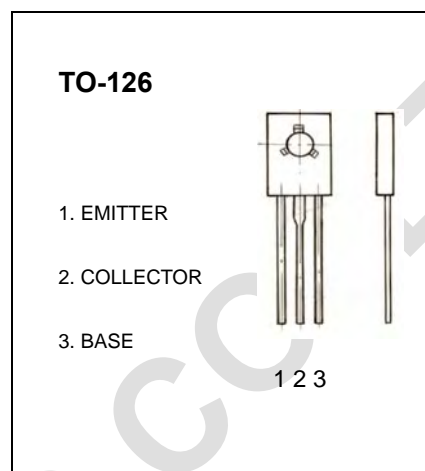
$I_{CM}$ : -2.5 A

Collector-base voltage

$V_{(BR)CBO}$ : -110 V

Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$



#### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-110			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-7			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-100V, I_E=0$			-1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-5V, I_C=0$			-1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE}=-2V, I_C=-100mA$	100		560	
	$h_{FE(2)}$	$V_{CE}=-2V, I_C=-1.5A$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2A, I_B=-200mA$			-0.5	V
Base-emitter voltage	$V_{BE}$	$V_{CE}=-5V, I_C=-500mA$			-1	V
Transition frequency	$f_T$	$V_{CE}=-1V, I_C=-250mA, f=1MHz$	3			MHZ

#### CLASSIFICATION OF $h_{FE(1)}$

Rank	R	S	T	U
Range	100-200	140-280	200-400	280-560